



v04.0505



P Designer's Kit

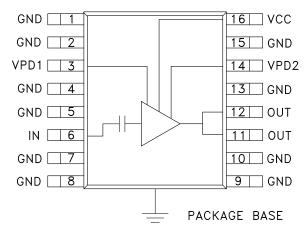
Available

Typical Applications

This amplifier is ideal for use as a power/driver amplifier for 1.6 - 2.2 GHz applications:

- Cellular / PCS / 3G
- Portable & Infrastructure
- Wireless Local Loop

Functional Diagram



GaAs InGaP HBT MMIC POWER AMPLIFIER, 1.6 - 2.2 GHz

Features

Gain: 23 dB Saturated Power: +29.5 dBm 42% PAE Supply Voltage: +2.75V to +5V Power Down Capability Low External Part Count Included in the HMC-DK002 Designer's Kit

General Description

The HMC413QS16G & HMC413QS16GE are high efficiency GaAs InGaP Heterojunction Bipolar Transistor (HBT) MMIC Power amplifiers which operate between 1.6 and 2.2 GHz. The amplifier is packaged in a low cost, surface mount 16 leaded package with an exposed base for improved RF and thermal performance. With a minimum of external components, the amplifier provides 23 dB of gain, +29.5 dBm of saturated power at 42% PAE from a +5V supply voltage. The amplifier can also operate with a 3.6V supply. Vpd can be used for full power down or RF output power/ current control.

Electrical Specifications, $T_A = +25^{\circ}$ C, As a Function of Vs, Vpd = 3.6V

Demenden	Frequency	Vs= 3.6V		Vs= 5V		11.11		
Parameter		Min.	Тур.	Max.	Min.	Тур.	Max.	Units
Gain	1.6 - 1.7 GHz 1.7 - 2.0 GHz 2.0 - 2.1 GHz 2.1 - 2.2 GHz	18 19 18 17	21 22 21 20		19 20 19 18	22 23 22 21		dB dB dB dB
Gain Variation Over Temperature	1.6 - 2.2 GHz		0.025	0.035		0.025	0.035	dB/°C
Input Return Loss	1.6 - 2.2 GHz		10			10		dB
Output Return Loss	1.6 - 2.2 GHz		8			9		dB
Output Power for 1 dB Compression (P1dB)	1.6 - 1.7 GHz 1.7 - 2.2 GHz	20 21	23 24		23 24	26 27		dBm dBm
Saturated Output Power (Psat)	1.6 - 1.7 GHz 1.7 - 2.2 GHz		25.5 26.5			28.5 29.5		dBm dBm
Output Third Order Intercept (IP3)	1.6 - 1.7 GHz 1.7 - 2.0 GHz 2.0 - 2.2 GHz	32 33 32	35 36 35		36 37 36	39 40 39		dBm dBm dBm
Noise Figure	1.6 - 2.2 GHz		5.5			5.5		dB
Supply Current (Icq) Vpd= 0V/3.6V			0.002/220			0.002/270		mA
Control Current (Ipd) Vpd= 3.6V			7			7		mA
Switching Speed tON, tOFF			80			80		ns

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HMC413* PRODUCT PAGE QUICK LINKS

Last Content Update: 02/23/2017

COMPARABLE PARTS

View a parametric search of comparable parts.

EVALUATION KITS

HMC413QS16G Evaluation Board

DOCUMENTATION

Application Notes

- AN-1363: Meeting Biasing Requirements of Externally Biased RF/Microwave Amplifiers with Active Bias Controllers
- Broadband Biasing of Amplifiers General Application Note
- MMIC Amplifier Biasing Procedure Application Note
- Thermal Management for Surface Mount Components General Application Note

Data Sheet

HMC413 Data Sheet

TOOLS AND SIMULATIONS \square

• HMC413 S-Parameter

REFERENCE MATERIALS

Quality Documentation

- HMC Legacy PCN: QS##, QS##E and QS##G,QS##GE packages Relocation of pre-existing production equipment to new building
- Package/Assembly Qualification Test Report: Plastic Encapsulated QSOP (QTR: 02015 REV: 11)
- PCN: MS, QS, SOT, SOIC packages Sn/Pb plating vendor change
- Semiconductor Qualification Test Report: GaAs HBT-B (QTR: 2013-00229)

DESIGN RESOURCES

- HMC413 Material Declaration
- PCN-PDN Information
- Quality And Reliability
- Symbols and Footprints

DISCUSSIONS

View all HMC413 EngineerZone Discussions.

SAMPLE AND BUY

Visit the product page to see pricing options.

TECHNICAL SUPPORT

Submit a technical question or find your regional support number.

DOCUMENT FEEDBACK

Submit feedback for this data sheet.



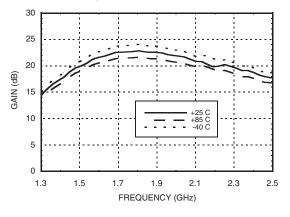
POWER AMPLIFIER, 1.6 - 2.2 GHz

GaAs InGaP HBT MMIC

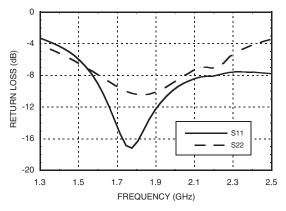
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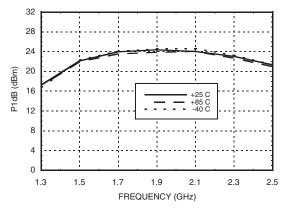
Gain vs. Temperature, Vs= 3.6V



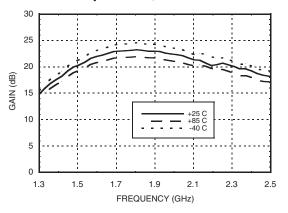
Return Loss, Vs= 3.6V



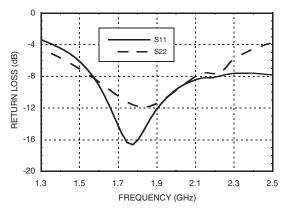
P1dB vs. Temperature, Vs= 3.6V



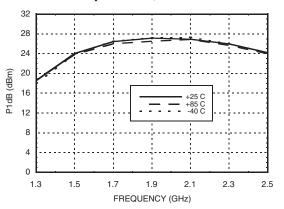
Gain vs. Temperature, Vs= 5V



Return Loss, Vs= 5V



P1dB vs. Temperature, Vs= 5V



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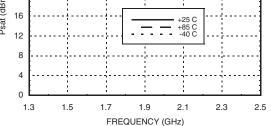
POWER AMPLIFIER, 1.6 - 2.2 GHz

GaAs InGaP HBT MMIC

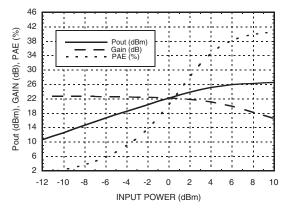
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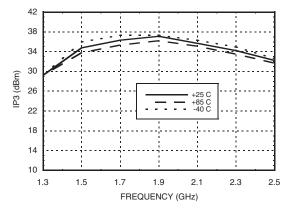
Psat vs. Temperature, Vs= 3.6V



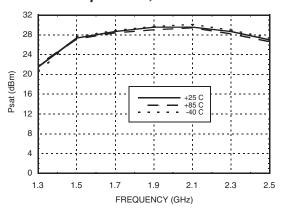
Power Compression@ 1.9 GHz, Vs= 3.6V



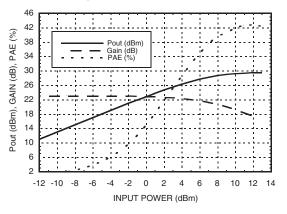
Output IP3 vs. Temperature, Vs= 3.6V



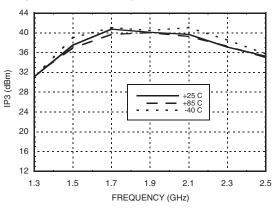
Psat vs. Temperature, Vs= 5V



Power Compression@ 1.9 GHz, Vs= 5V



Output IP3 vs. Temperature, Vs= 5V



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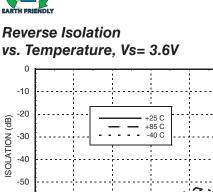
11 - 52



BoHS

HMC413QS16G / 413QS16GE

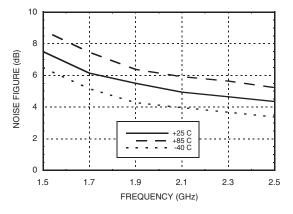
GaAs InGaP HBT MMIC POWER AMPLIFIER, 1.6 - 2.2 GHz



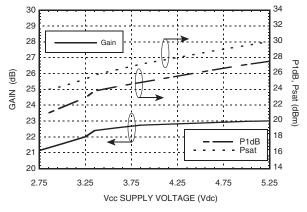
-40 -50 -60 -70 1.3 1.5 1.7 1.9 2.1 2.3 2.5 FREQUENCY (GHz)

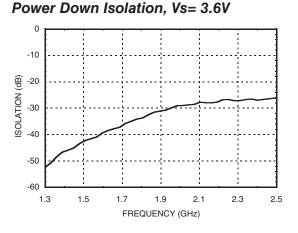
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Noise Figure vs. Temperature, Vs= 3.6V

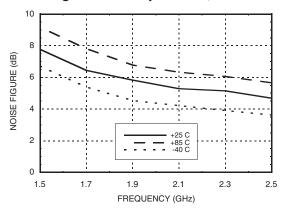


Gain & Power vs. Supply Voltage @ 1.9 GHz

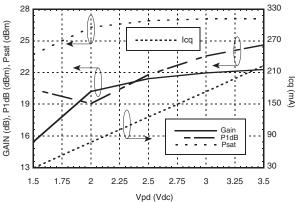




Noise Figure vs. Temperature, Vs= 5V







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GaAs InGaP HBT MMIC POWER AMPLIFIER, 1.6 - 2.2 GHz



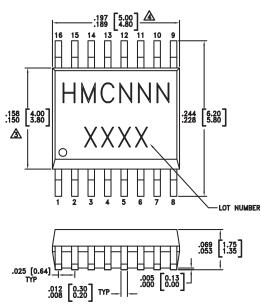
Absolute Maximum Ratings

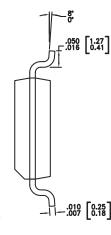
+5.5 Vdc
+4.0 Vdc
+15 dBm
150 °C
1.56 W
42 °C/W
-65 to +150 °C
-40 to +85 °C

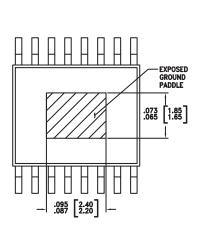
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Outline Drawing







NOTES:

1. LEADFRAME MATERIAL: COPPER ALLOY

2. DIMENSIONS ARE IN INCHES [MILLIMETERS].

A DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.15mm PER SIDE.

A DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.25mm PER SIDE.

 5. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.

Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking ^[3]
HMC413QS16G	Low Stress Injection Molded Plastic	Sn/Pb Solder	MSL1 ^[1]	HMC413 XXXX
HMC413QS16GE	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 [2]	HMC413 XXXX

[1] Max peak reflow temperature of 235 $^\circ\text{C}$

[2] Max peak reflow temperature of 260 $^\circ\text{C}$

[3] 4-Digit lot number XXXX

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GaAs InGaP HBT MMIC POWER AMPLIFIER, 1.6 - 2.2 GHz



Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1, 2, 4, 5, 7, 8, 9, 10, 13, 15	GND	Ground: Backside of package has exposed metal ground slug that must be connected to ground thru a short path. Vias under the device are required.	
3, 14	Vpd1, Vpd2	Power Control Pin. For maximum power, this pin should be connected to 3.6V. For 5V operation, a dropping resistor is required. A higher voltage is not recommended. For lower idle current, this voltage can be reduced.	VPD1 VPD2
6	RFIN	This pin is AC coupled and matched to 50 Ohms from 1.6 to 2.2 GHz.	
11, 12	RFOUT	RF output and bias for the output stage.	
16	Vcc	Power supply voltage for the first amplifier stage. An external bypass capacitor of 330 pF is required as shown in the application schematic.	VCC1 VCC2

LINEAR & POWER AMPLIFIERS - SMT

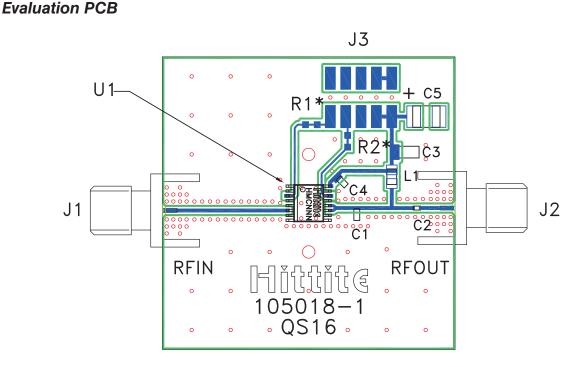
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GaAs InGaP HBT MMIC POWER AMPLIFIER, 1.6 - 2.2 GHz



* For 5V operation on Vctl line, select R1, R2 such that 3.6V is presented on Pins 3 and 14.

List of Materials for Evaluation PCB 105000 [1]

Item	Description	
J1 - J2	PCB Mount SMA RF Connector	
J3	2 mm DC Header	
C1	2.2 pF Capacitor, 0603 Pkg.	
C2	10 pF Capacitor, 0402 Pkg.	
C3 - C4	330 pF Capacitor, 0603 Pkg.	
C5	2.2 µF Capacitor, Tantalum	
L1	16 nH Inductor 0603 Pkg.	
U1	HMC413QS16G / HMC413QS16GE Amplifier	
PCB [2]	105018 Eval Board	

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

The circuit board used in the final application should use RF circuit design techniques. Signal lines should have 50 ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.

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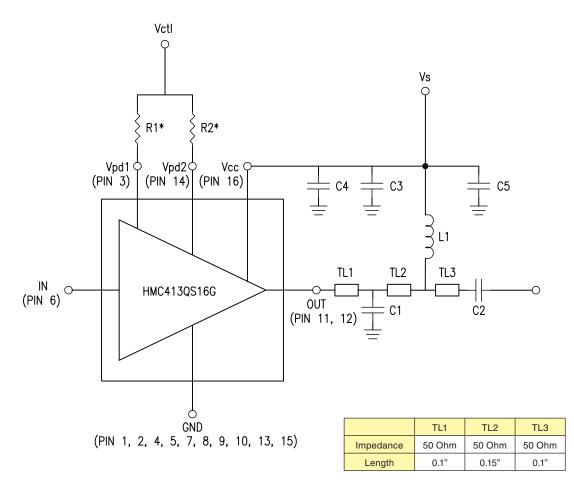


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GaAs InGaP HBT MMIC POWER AMPLIFIER, 1.6 - 2.2 GHz

Application Circuit



* For 5V operation on Vctl line, select R1, R2 such that 3.6V is presented on Pins 3 and 14.

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